

45. A method as defined in claim 44, wherein said device comprises a gas pipe having a plurality of gas outlets.

46. A method for heat treating a semiconductor wafer, said method comprising the steps of:

placing a semiconductor wafer in a thermal processing chamber, said semiconductor wafer defining a plurality of localized regions along a radial axis;

adjusting the temperature of said semiconductor wafer using a plurality of lamps to a predetermined temperature according to a predetermined heat cycle, said predetermined heat cycle including a heat stage;

during at least one stage of predetermined heat cycle, providing a gas to selectively control the temperature of at least one of said localized regions of said semiconductor wafer to minimize temperature deviation of said at least one localized region from said predetermined temperature, said gas being supplied by a reflective device located below said semiconductor wafer.

47. A method as defined in claim 46, wherein a plurality of gas outlets extend through said reflective device.

48. A method for heat treating a semiconductor wafer, said method comprising the steps of:

placing a semiconductor wafer in a thermal processing chamber, said semiconductor wafer defining a plurality of localized regions along a radial axis;

adjusting the temperature of said semiconductor wafer using a plurality of lamps to a predetermined temperature according to a predetermined heat cycle, said predetermined heat cycle including a heat stage;